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Supplementary Material

Theoretical Study on the Effects of Alloying Elements on TiO_2/Ti_2AlNb Interface Adhesion Properties

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Figure S4. Differential charge densities of the bare TiO_2/Ti_2AlNb interface during normal separation

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Figure S6. Differential charge densities of the Hf element doped (Nb substituted) TiO₂/Ti₂AlNb interface during normal separation

Figure S7. The relaxation process of first-principles molecular dynamics Figure S8. Structural changes of the TiO_2/Ti_2AINb interface at 1100K





Fig. 1 Convergence of cutoff energy and k-mesh





Fig. 2 a) W_{sep}-distance curve and b) stress-strain curve of normal separation process of alloying elements doped (Al substituted) TiO₂/Ti₂AlNb interface, c) W_{sep}-distance curve and d) stress-strain curve of normal separation process of alloying elements doped (Ti substituted) TiO₂/Ti₂AlNb interface, e) W_{sep}-distance curve and f) stress-strain curve of normal separation process of alloying elements doped (Nb substituted) TiO₂/Ti₂AlNb interface





Fig. 3 a) W_{sep} -distance curve and b) stress-strain curve of tangential separation process of alloying elements doped (Al substituted) TiO₂/Ti₂AlNb interface, c) W_{sep} -distance curve and d) stress-strain curve of tangential separation process of alloying elements doped (Ti substituted) TiO₂/Ti₂AlNb interface, e) W_{sep} -distance curve and f) stressstrain curve of tangential separation process of alloying elements doped (Nb substituted) TiO₂/Ti₂AlNb interface



Fig. 4 Differential charge densities of the bare TiO₂/Ti₂AlNb interface during normal separation, a) Strain value of 0%, b) Strain value of 1.46%, c) Strain value of 3.65%, d) Strain value of 7.3%



Fig. 5 Differential charge densities of the Si element doped (Nb substituted)
TiO₂/Ti₂AlNb interface during normal separation, a) Strain value of 0%, b) Strain value of 1.46%, c) Strain value of 3.65%, d) Strain value of 7.3%



Fig. 6 Differential charge densities of the Hf element doped (Nb substituted)
TiO₂/Ti₂AlNb interface during normal separation, a) Strain value of 0%, b) Strain value of 1.46%, c) Strain value of 3.65%, d) Strain value of 7.3%





Fig. 7 The relaxation process of first-principles molecular dynamics, a) the bare TiO_2/Ti_2AINb interface, b) the Si doped TiO_2/Ti_2AINb interface, c) the Hf doped TiO_2/Ti_2AINb interface



Fig. 8 Structural changes of the TiO_2/Ti_2AINb interface at 1100K, a) the bare TiO_2/Ti_2AINb interface, b) the Si doped TiO_2/Ti_2AINb interface, c) the Hf doped TiO_2/Ti_2AINb interface